

- High-Resolution Conversion of Light Intensity to Frequency With No External Components
- Direct Interface With a Microcontroller
- Compact Three-Leaded Plastic Package
- Single-Supply Operation Down to 2.7 V
- Nonlinearity Error Typically 0.2% at 100 kHz
- Advanced LinCMOS™ Technology
- Integral Visible-Light Cutoff Filter

## description

The TSL245 infrared light-to-frequency converter combines a silicon photodiode and a current-to-frequency converter on a single monolithic CMOS integrated circuit. The output is a square wave (50% duty cycle) with frequency directly proportional to light intensity. Because the output is TTL compatible, it allows direct interface to a microcontroller or other logic circuitry. The device responds over the infrared light range of 800 nm to 1100 nm. The TSL245 is characterized for operation over the temperature range of  $-25^{\circ}\text{C}$  to  $70^{\circ}\text{C}$ .

The TSL245 is offered in a black, infrared-transmissive package (see Figure 1). The photodiode area is  $1.36\text{ mm}^2$  ( $0.0029\text{ in}^2$ ).

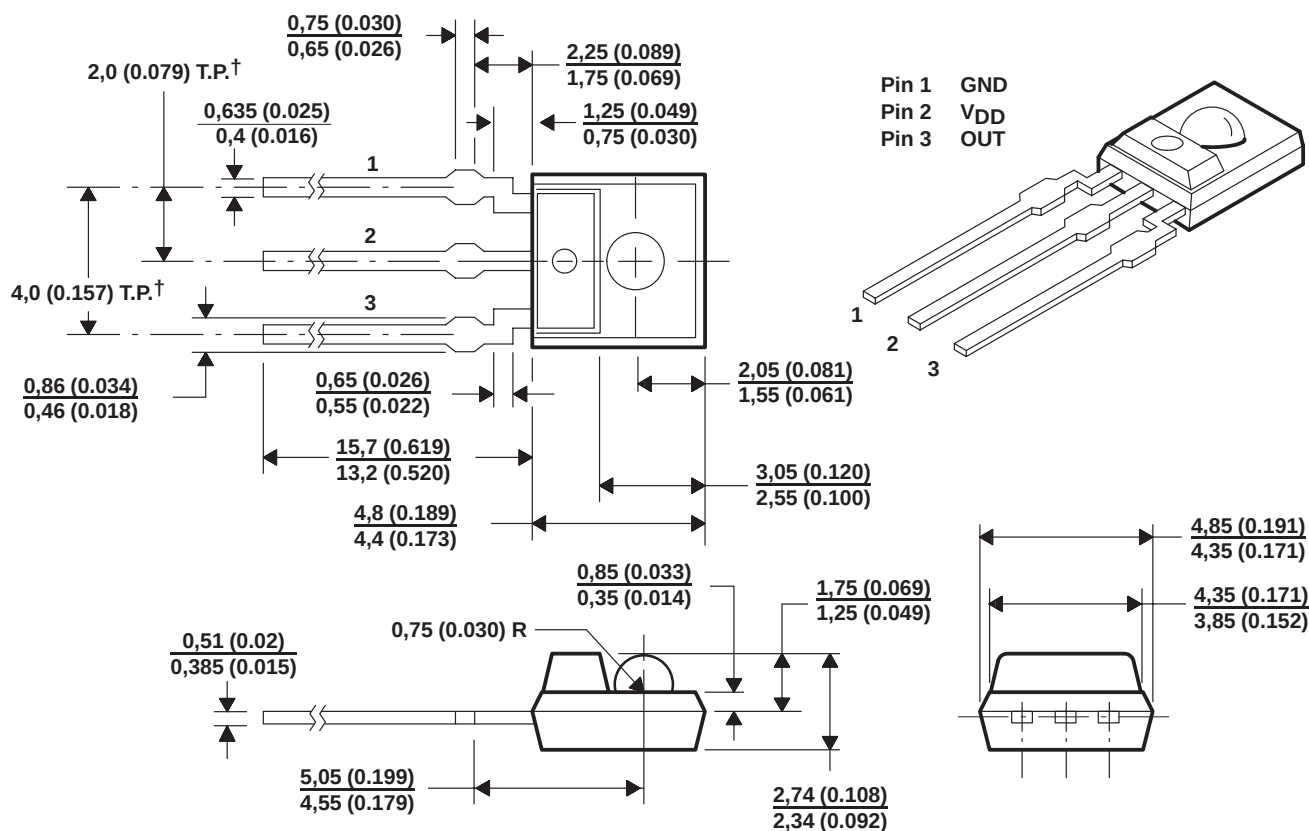


Figure 1. TSL245 Packaging Configuration

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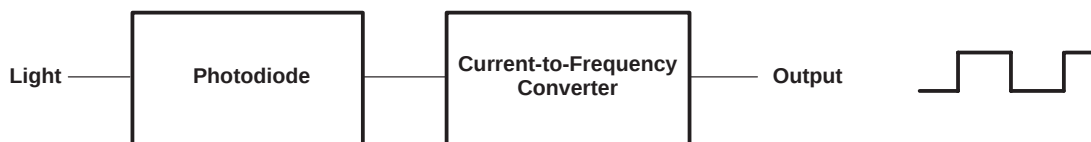
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# TSL245

## INFRARED LIGHT-TO-FREQUENCY CONVERTER

SOES018 – MAY 1995

### functional block diagram



### absolute maximum ratings over operating free-air temperature range (unless otherwise noted)<sup>†</sup>

|                                                              |               |
|--------------------------------------------------------------|---------------|
| Supply voltage, $V_{DD}$ (see Note 1)                        | 6.5 V         |
| Operating free-air temperature range, $T_A$                  | –25°C to 70°C |
| Storage temperature range, $T_{stg}$                         | –25°C to 85°C |
| Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds | 260°C         |

<sup>†</sup> Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: All voltage values are with respect to GND.

### recommended operating conditions

|                                             | MIN | NOM | MAX | UNIT |
|---------------------------------------------|-----|-----|-----|------|
| Supply voltage, $V_{DD}$                    | 2.7 | 5   | 6   | V    |
| Operating free-air temperature range, $T_A$ | –25 |     | 70  | °C   |

### electrical characteristics at $V_{DD} = 5$ V, $T_A = 25^\circ\text{C}$ (unless otherwise noted)

| PARAMETER                            | TEST CONDITIONS           | MIN | TYP  | MAX  | UNIT |
|--------------------------------------|---------------------------|-----|------|------|------|
| $V_{OH}$ High-level output voltage   | $I_{OH} = -4$ mA          | 4   | 4.3  |      | V    |
| $V_{OL}$ Low-level output voltage    | $I_{OL} = 4$ mA           |     | 0.17 | 0.26 | V    |
| $I_{DD}$ Supply current              |                           |     | 2    | 3    | mA   |
| Full-scale frequency <sup>‡</sup>    |                           | 500 |      |      | kHz  |
| $k_{SVS}$ Supply-voltage sensitivity | $V_{DD} = 5$ V $\pm 10\%$ |     | 0.5  |      | %/V  |

<sup>‡</sup> Full-scale frequency is the maximum operating frequency of the device without saturation.

### operating characteristics at $V_{DD} = 5$ V, $T_A = 25^\circ\text{C}$

| PARAMETER                              | TEST CONDITIONS                                            | MIN                                           | TYP         | MAX | UNIT  |
|----------------------------------------|------------------------------------------------------------|-----------------------------------------------|-------------|-----|-------|
| $f_O$ Output frequency                 | $E_e = 920 \mu\text{W}/\text{cm}^2$ , $\lambda_p = 940$ nm | 200                                           | 250         | 300 | kHz   |
|                                        | $E_e = 0$                                                  |                                               | 0.25        | 10  | Hz    |
| Nonlinearity <sup>§</sup>              | $f_O = 0$ kHz to 10 kHz                                    |                                               | $\pm 0.1\%$ |     | %F.S. |
|                                        | $f_O = 0$ kHz to 100 kHz                                   |                                               | $\pm 0.2\%$ |     | %F.S. |
| Step response to full-scale step input |                                                            | 1 pulse of new frequency plus 1 $\mu\text{s}$ |             |     |       |

<sup>‡</sup> Full-scale frequency is the maximum operating frequency of the device without saturation.

<sup>§</sup> Nonlinearity is defined as the deviation of  $f_O$  from a straight line between zero and full scale, expressed as a percent of full scale.

TYPICAL CHARACTERISTICS

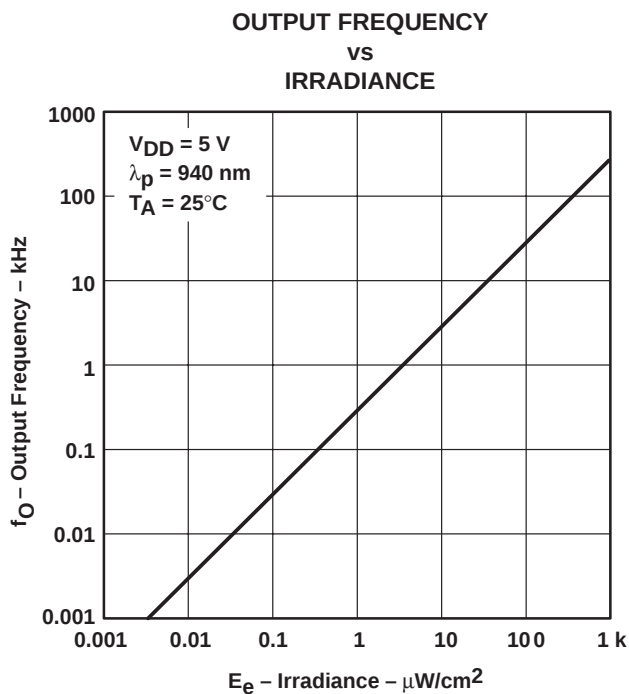


Figure 2

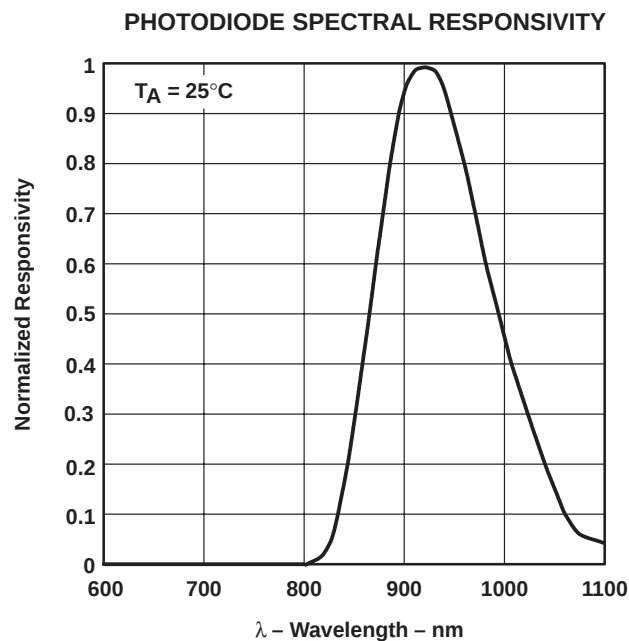


Figure 3

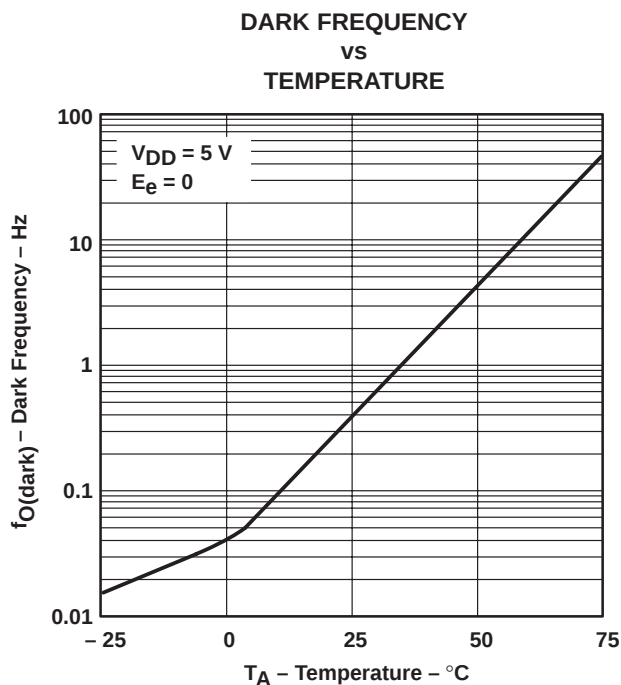


Figure 4

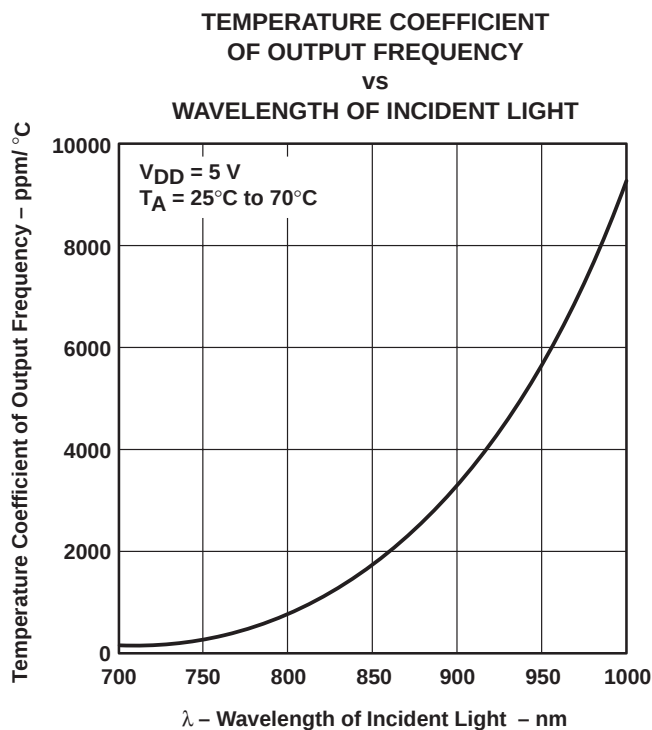


Figure 5

# TSL245

## INFRARED LIGHT-TO-FREQUENCY CONVERTER

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### TYPICAL CHARACTERISTICS

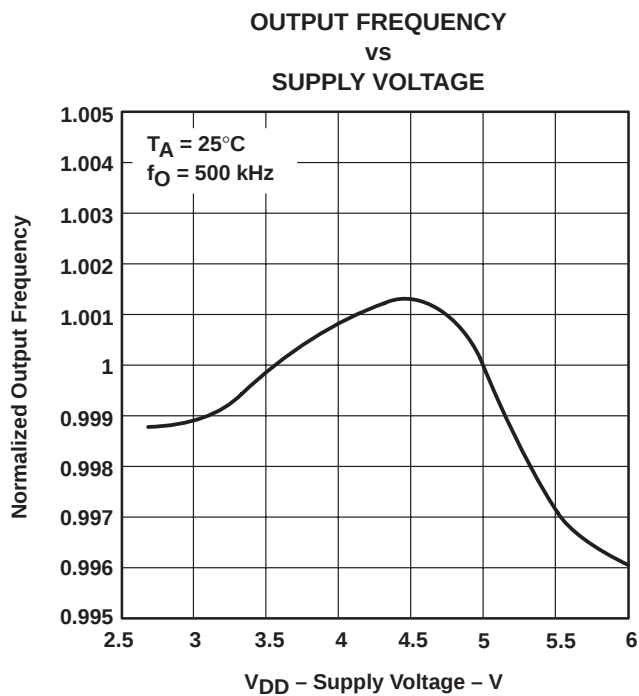


Figure 6

## APPLICATION INFORMATION

### power-supply considerations

For optimum device performance, power-supply lines should be decoupled by a 0.01- $\mu$ F to 0.1- $\mu$ F capacitor with short leads (see Figure 7).

### output interface

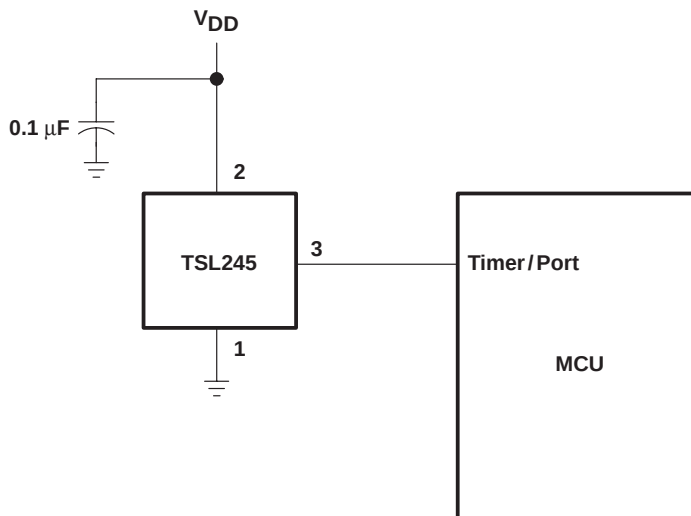
The output of the device is designed to drive a standard TTL or CMOS logic input over short distances. If lines greater than 12 inches are used on the output, a buffer or line driver is recommended.

### measuring the frequency

The choice of interface and measurement techniques depends on the desired resolution and data-acquisition rate. For maximum data-acquisition rate, period-measurement techniques should be used.

Period measurement requires using a fast reference clock with available resolution directly related to reference clock rate. The technique measures rapidly varying light levels or provides a fast measurement of a constant light source.

Maximum resolution and accuracy can be obtained using frequency-measurement, pulse-accumulation, or integration techniques. Frequency measurements provide the added benefit of averaging random- or high-frequency variations (jitter) resulting from noise in the light signal. Resolution is limited primarily by available counter registers and allowable measurement time. Frequency measurement is well suited for slowly varying or constant light levels and for reading average light levels over short periods of time. Integration, the accumulation of pulses over a very long period of time, can be used to measure exposure – the amount of light present in an area over a given time period.



**Figure 7. Typical TSL245 Interface to a Microcontroller**

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